

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Naoto Kusumoto et al.                      Art Unit : Unknown  
Serial No. : New Continuation App                      Examiner : Unknown  
Filed : June 25, 2003  
Title : LASER ANNEALING METHOD

Commissioner for Patents  
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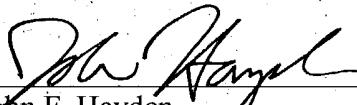
**INFORMATION DISCLOSURE STATEMENT**

Under 35 USC §120, this application relies on the earlier filing date of application serial number 08/594,670, filed on February 2, 1996. The attached list of references were submitted to and/or cited by the Office in the prior application and, therefore, are not provided in this application.

This statement is being filed with the application. Please apply any charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Date: June 25, 2003

  
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Substitute Form PTO-1449 (Modified)  <b>Information Disclosure Statement by Applicant</b> (Use several sheets if necessary)  (37 CFR §1.98(b))	U.S. Department of Commerce Patent and Trademark Office		Attorney's Docket No. 07977-004002	Application No. New Continuation Application
	Applicant Naoto Kusumoto et al.			
	Filing Date June 25, 2003		Group Art Unit	

## U.S. Patent Documents

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA	3,585,088	06/1971	Scwuttke et al.			
	AB	4,195,913	4/1/80	Dourte et al.			
	AC	4,475,027	10/2/84	Pressley			
	AD	5,145,808	09/1995	Sameshima et al.			
	AE	5,219,786	6/15/93	Noguchi			
	AF	5,304,357	04/1994	Sato et al.			
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	AT	6,358,784	03/19/2002	Zhang, et al			

## Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
	AU	ZA8306334	03/1984	China				
	AV	64-76715	03/1989	Japan				
	AW	1-76715	03/1989	Japan				
	AX	3-286518	12/1991	Japan				

Examiner Signature	Date Considered
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

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							Yes	No
	AY	4-307727	10/1992	Japan				

<b>Other Documents (include Author, Title, Date, and Place of Publication)</b>		
Examiner Initial	Desig. ID	Document
	AZ	Anderson et al.; "Characterization of the substrate interface of excimer laser crystallized polysi..."; <i>MRS Symp. Proc.</i> 343; pp. 709; 1994
	AAA	Brotherton et al.; "Beam shape effects with EL crystallization of...a-Si"; <i>Solid State Phenomena</i> ; pp. 37-38; 1994
	ABB	Carluccio et al., "Microstructure of Polycrystalline Silicon Films Obtained by Combined Furnace and Laser Annealing", <i>Appl. Phys. Lett.</i> , Vol. 66, No. 11, pp. 1394-1396
	ACC	Caune et al.; "Combined CW laser and furnace annealing of a-Si and Ge in contact with some metals"; <i>Appl. Surf. Sci.</i> 36; p. 597; 1989
	ADD	Hayashi et al.; "Fabrication of Low-Temperature Bottom-Gate Poly-Si TFTs on Large-Area Substrate by Linear-Beam Excimer Laser Crystallization and Ion Doping Method"; <i>IEEE IEDM</i> ; pp. 829-832; 1995
	AEE	Jhon et al.; "Crystallization of Amorphous Silicon by Excimer Laser Annealing with a Line Shape Beam Having a Gaussian Profile"; <i>Japan Journal of Applied Physics</i> , Vol. 33; pp. 1438-1441; October 1994
	AFF	Jhon et al.; "Crystallization of a-Si by ELA with a line shape beam having a Gaussian profile"; <i>Jpn. J. Appl. Phys</i> 33(10B); p. L1438; October 1994
	AGG	Kohno et al., "High Performance Poly-Si TFTs Fabricated Using Pulsed Laser Annealing and Remote Plasma CVD with Low Temperature Processing", <i>IEEE Transactions on Electron Devices</i> , Vol. 42, No. 2, pp. 251-257
	AHH	Kuriyama et al.; "Improving...ELA method for giant microelectronics"; <i>Jpn. J. Appl. Phys.</i> 31(12B); p. 4550; December 1992
	AII	Kuriyama et al.; "Lateral growth of Poly-Si films...by ELA..."; <i>Jpn. J. Appl. Phys.</i> 32(12B); p. 6190; December 1993
	AJJ	Okumura et al.; "Excimer laser annealed poly-Si TFT technologies"; <i>MRS Symp. Proc.</i> 377; p. 877; April 1995
	AKK	Sweatt; "Transforming a circular laser beam into a square or trapezoid..."; <i>Optical Eng.</i> 31(2); p. 245; February 1992

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